JMD100TD18D1W

Three Phase Rectifier Bridge Module

Features

- Low forward voltage and leakage current
- Low inductance package
- High surge current capability

Product Summary

Parameter	Value	Unit
V_{RRM}	1800	V
I_D	100	A
I_{FSM}(@ t_P = 10ms)	1100	

Applications

- Field supply for DC motors
- Line rectifiers for transistorized AC motor controllers
- Non-controllable rectifiers for AC/DC converter

Absolute Maximum Ratings (@ T_C = 25℃ unless otherwise specified)

Parameter	Conditions	Symbol	Values	Unit
Repetitive peak reverse voltage		V_{RRM}	1800	V
Non-repetitive peak reverse voltage		V_{RSM}	1900	V
Output current	T_C = 100	I_D	100	A
Forward surge current	1/2 cycle, Sine wave, 50Hz T_{vj} = 25	I_{FSM}	1100	A
I^2t value for fusing		I^2t	6050	A^2s
RMS isolation voltage	A.C 50Hz(1s/1min)	V_{ISO}	3600/3000	V
Junction temperature range		T_J	-40 ~ +150	
Storage temperature range		T_{stg}	-40 ~ +125	

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Electrical Characteristics (@ T_C = 25℃ unless otherwise specified)

Parameter	Conditions	Symbol	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	I_F = 100A, Tvj = 25	V_F		1.15	1.35	V
Reverse leakage current	$V_R = V_{RRM}$, Tvj = 25	I_{RRM}			0.5	mA
	$V_R = V_{RRM}$, Tvj = 150				10	mA
Threshold voltage	For power loss calculation only Tvj = 150 ,	V_{TO}			0.82	V
Dynamic resistance		r_T			3.3	mΩ

Thermal Characteristics (@ T_C = 25℃ unless otherwise specified)

Parameter	Conditions	Symbol	Values			Unit

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